

SEMICONDUCTOR TECHNICAL DATA

2N3904

EPITAXIAL PLANAR NPN TRANSISTOR

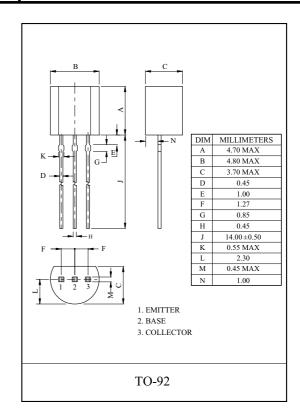
GENERAL PURPOSE APPLICATION. SWITCHING APPLICATION.

FEATURES

- · Low Leakage Current
 - : I_{CEX} =50nA(Max.), I_{BL} =50nA(Max.) @ V_{CE} =30V, V_{EB} =3V.
- · Excellent DC Current Gain Linearity.
- · Low Saturation Voltage
 - : $V_{CE(sat)} = 0.3V(Max.)$ @ $I_C = 50mA$, $I_B = 5mA$.
- · Low Collector Output Capacitance
 - : C_{ob} =4pF(Max.) @V_{CB}=5V.
- · Complementary to 2N3906.

MAXIMUM RATING (Ta=25 ℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		V _{CBO}	60	V	
Collector-Emitter Voltage		V _{CEO}	40	V	
Emitter-Base Voltage		$V_{\rm EBO}$	6	V	
Collector Current		I_C	200	mA	
Base Current		I_{B}	50	mA	
Collector Power	ollector Power Ta=25 °C P _C		625	mW	
Dissipation	Tc=25 ℃	1 C	1.5	W	
Junction Temperature		T _j	150	$^{\circ}$ C	
Storage Temperature Range		T_{stg}	-55 ~ 150	$^{\circ}$	



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ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACT	ERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Curi	rent	I_{CEX}	$V_{CE}=30V, V_{EB}=3V$	-	-	50	nA	
Base Cut-off Current		I_{BL}	V _{CE} =30V, V _{EB} =3V		-	50	nA	
Collector-Base Break	down Voltage	V _{(BR)CBO}	$I_{C}=10\mu A,\ I_{E}=0$	60	-	-	V	
Collector-Emitter Brea	akdown Voltage *	V _{(BR)CEO}	$I_{\rm C}=1{\rm mA},\ I_{\rm B}=0$		-	-	V	
Emitter-Base Breakdown Voltage		V _{(BR)EBO}	$I_{E}=10\mu A,\ I_{C}=0$	6.0	-	-	V	
DC Current Gain *		h _{FE} (1)	V _{CE} =1V, I _C =0.1mA	40	-	-		
		h _{FE} (2)	V _{CE} =1V, I _C =1mA	70	-	-		
		h _{FE} (3)	$V_{CE}=1V$, $I_{C}=10mA$	100	-	300		
		h _{FE} (4)	$V_{CE}=1V$, $I_{C}=50$ mA	60	-	-		
		h _{FE} (5)	V _{CE} =1V, I _C =100mA	30	-	-		
Collector-Emitter Saturation Voltage *		V _{CE(sat)} 1	I _C =10mA, I _B =1mA	-	-	0.2	17	
		V _{CE(sat)} 2	I _C =50mA, I _B =5mA	-	-	0.3	V	
Base-Emitter Saturation Voltage *		V _{BE(sat)} 1	I _C =10mA, I _B =1mA	0.65	-	0.85	· V	
		V _{BE(sat)} 2	I _C =50mA, I _B =5mA	-	-	0.95		
Transition Frequency		f_T	V _{CE} =20V, I _C =10mA, f=100MHz	300	-	-	MHz	
Collector Output Capacitance		C _{ob}	$V_{CB}=5V$, $I_{E}=0$, $f=1MHz$	-	-	4.0	pF	
Input Capacitance		C _{ib}	V _{BE} =0.5V, I _C =0, f=1MHz	-	-	8.0	pF	
Input Impedance		h _{ie}	V _10V I _1 _ A _ f_1 J J	1.0	-	10	kΩ	
Voltage Feedback Ratio		h _{re}		0.5	-	8.0	x10-4	
Small-Signal Current Gain		h _{fe}	$V_{CE}=10V$, $I_{C}=1$ mA, $f=1$ kHz	100	-	400		
Collector Output Admittance		h _{oe}		1.0	-	40	μ \(\tau \)	
Noise Figure		NF	V_{CE} =5V, I_{C} =0.1mA Rg=1k Ω , f=10Hz \sim 15.7kHz	-	-	5.0	dB	
Switching Time	Delay Time	t _d	V_{in} o V_{out} $V_{$	-	-	35	25	
	Rise Time	t _r	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	-	35		
	Storage Time	t _{stg}	V_{in} O	-	-	200	nS	
	Fall Time	t _f	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	-	-	50		

^{*} Pulse Test : Pulse Width ≤300 µS, Duty Cycle ≤2%.

